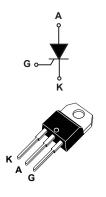


16 A 600 V high temperature SCR thyristors in insulated TO-220



TO-220AB insulated

Features

- High junction temperature: T_j = 150 °C
- High noise immunity dV/dt = 1000 V/µs up to 150 °C
- Peak off-state voltage V_{DRM}/V_{RRM} = 600 V
- High turn-on current rise dI/dt = 100 A/µs
- · Insulated package TO-220AB:
 - Insulated voltage: 2500 V_{RMS}
 - Complies with UL 1557 (File ref : E81734)
- ECOPACK2 compliant
- · Halogen-free molding, lead-free plating

Applications

- General purpose AC line load switching
- · Motor control circuits and starters
- · Inrush current limiting circuits
- · Heating resistor control, solid state relays

Description

Thanks to its operating junction temperature up to 150° C, the TN1610H-6I offers high thermal performance operation up to 16 A rms.

Its trade-off noise immunity (dV/dt = 1000 V/ μ s) versus its gate triggering current (I_{GT} = 10 mA) and its turn-on current rise (dI/dt = 100 A/ μ s) allows to design robust and compact control circuit for voltage regulator in motorbikes and industrial drives, overvoltage crowbar protection, motor control circuits in power tools and kitchen appliances and inrush current limiting circuits.

Product status	
TN1610H-6I	

Product summary			
Order code	TN1610H-6I		
Package	TO-220AB Ins.		
I _{T(RMS)}	16 A		
V_{DRM}/V_{RRM}	600 V		
T _j max.	150 °C		



1 Characteristics

Table 1. Absolute maximum ratings (limiting values), T_j = 25 °C unless otherwise specified

Symbol	Parameter			Value	Unit
I _{T(RMS)}	RMS on-state current (180 ° conduction angle)		T _c = 116 °C	16	Α
			T _c = 116 °C	10	
$I_{T(AV)}$	Average on-state current (180 ° cond	Average on-state current (180 ° conduction angle)		8	Α
				6	
I _{TSM}	Non repetitive surge peak on-state co	urrent (T. initial = 25 °C)	t _p = 8.3 ms	153	_
TSM	Non repetitive surge peak on-state of	urrent (1) miliar – 25 °C)	t _p = 10 ms	140	A
l ² t	I ² t value for fusing, (T _j initial = 25 °C)	l^2 t value for fusing, (T_j initial = 25 °C) t_p			A ² s
dl/dt	I _G = 2 x I _{GT} , tr ≤ 100 ns		f = 60 Hz	100	A/µs
ui/ut	Critical rate of rise of on-state current		1 – 60 HZ	100	Ανμδ
V_{DRM}/V_{RRM}	Repetitive peak off-state voltage			600	V
V_{DSM}/V_{RSM}	Non Repetitive peak off-state voltage		t _p = 10 ms	V _{DRM} /V _{RRM} + 100 V	V
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 150 °C	4	Α
P _{G(AV)}	Average gate power dissipation		T _j = 150 °C	1	W
V_{RGM}	Maximum peak reverse voltage			5	V
T _{stg}	Storage junction temperature range			-40 to +150	°C
Tj	Maximum operating junction temperature			-40 to +150	°C
T _I	Maximum lead temperature soldering during 10 s			260	°C
V _{iso}	Insulation rms voltage, 1 minute			2500	V

Table 2. Electrical characteristics (T_j = 25 °C unless otherwise specified)

Symbol	Test conditions				Unit
I _{GT}			Тур.	4.5	mA
'GT	$V_D = 12 \text{ V}, R_L = 33 \Omega$		Max.	10	IIIA
V _{GT}			Max.	1.3	V
V_{GD}	$V_D = V_{DRM}$, $R_L = 3.3 \text{ k}\Omega$	T _j = 150 °C	Min.	0.2	V
I _H	I _T = 500 mA, gate open				mA
IL	$I_G = 1.2 \times I_{GT}$		Max.	60	mA
dV/dt	V _D = 402 V, gate open	T _j = 150 °C	Min.	1000	V/µs
t _{gt}	$I_T = 32 \text{ A}, V_D = 402 \text{ V}, I_G = 20 \text{ mA}, (dI_G/dt) \text{ max} = 0.2 \text{ A/}\mu\text{s}$			1.9	μs
t _q	I_T = 16 A, V_D = 402 V, (d I_G /dt) max = 30 A/ μ s, V_R = 25 V, d V_D /dt = 40 V/ μ s I_j = 150 °C			70	μs

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Table 3. Static characteristics

Symbol	Test conditions			Value	Unit
V _{TM}	I _T = 32 A, t _p = 380 μs	T _j = 25 °C	Max.	1.60	V
V _{TO}	Threshold voltage	T _j = 150 °C	Max.	0.82	V
R _D	Dynamic resistance	T _j = 150 °C	Max.	25	mΩ
J J	V- = V: V- = V	T _j = 25 °C	Mari	5	μA
I_{DRM} , I_{RRM} $V_D = V_{DRM}$; $V_R = V_{RRM}$		T _j = 150 °C	Max.	1.5	mA

Table 4. Thermal parameters

Symbol	Parameter	Value	Unit	
R _{th(j-c)}	Junction to case (DC)	Max.	2.3	°CAM
R _{th(j-a)}	Junction to ambient (DC)	Тур.	60	°C/W

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1.1 Characteristics curves

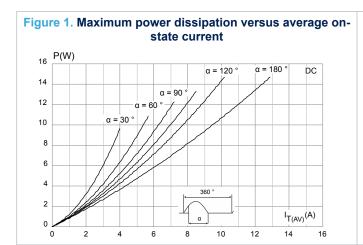


Figure 2. Average and DC on-state current versus case temperature $I_{T(AV)}(A)$ 18 D.C 16 14 12 α = $\alpha = 30^{\circ}$ 10 8 6 0 0 25 50 75 100 125 150

Figure 3. Average and D.C. on state current versus ambient temperature

IT(AV)(A)

2.5

2

0

1.5

1

0.5

0

0

25

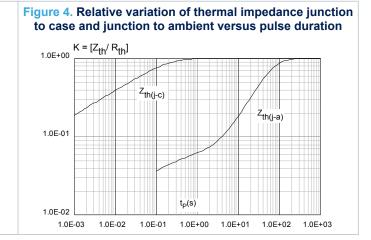
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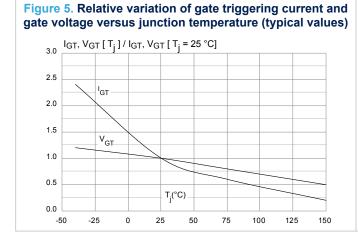
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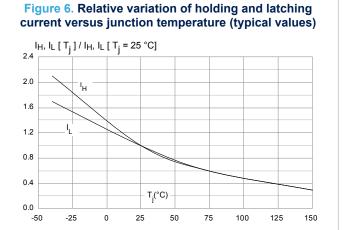
100

125

150







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Figure 7. Relative variation of static dV/dt immunity versus junction temperature

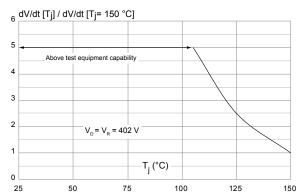


Figure 8. Surge peak on-state current versus number of cycles

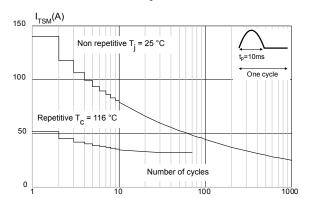


Figure 9. Non repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10$ ms

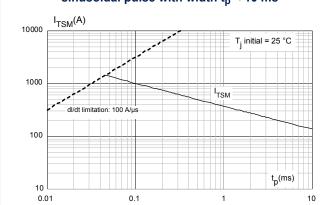


Figure 10. On-state characteristics (maximum values)

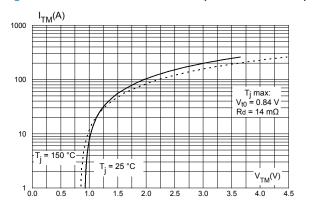
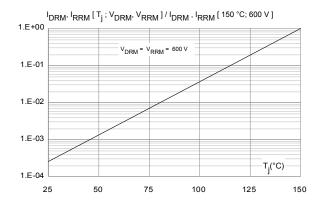


Figure 11. Relative variation of leakage current versus junction



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2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

2.1 TO-220AB insulated package information

- Molding compound resin is halogen-free and meets flammability standard UL94 level 0
- · Lead-free package leads finishing
- ECOPACK2 compliant
- Recommended torque: 0.4 to 0.6 N.m

С В b2 Resin gate 0.5 mm max. protusion(1 F Α 14 13 c2 a1 12 a2 M c1 Resin gate 0.5 mm b1 max. protusion⁽¹⁾

Figure 12. TO-220AB insulated package outline

(1) Resin gate position accepted in one of the two positions or in the symmetrical opposites.

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Table 5. TO-220AB insulated package mechanical data

	Dimensions					
Ref.		Millimeters		Inches ⁽¹⁾		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	15.20		15.90	0.5984		0.6260
a1		3.75			0.1476	
a2	13.00		14.00	0.5118		0.5512
В	10.00		10.40	0.3937		0.4094
b1	0.61		0.88	0.0240		0.0346
b2	1.23		1.32	0.0484		0.0520
С	4.40		4.60	0.1732		0.1811
c1	0.49		0.70	0.0193		0.0276
c2	2.40		2.72	0.0945		0.1071
е	2.40		2.70	0.0945		0.1063
F	6.20		6.60	0.2441		0.2598
1	3.73		3.88	0.1469		0.1528
L	2.65		2.95	0.1043		0.1161
12	1.14		1.70	0.0449		0.0669
13	1.14		1.70	0.0449		0.0669
14	15.80	16.40	16.80	0.6220	0.6457	0.6614
М		2.6			0.1024	

^{1.} Inch dimensions are for reference only.

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3 Ordering information

Figure 13. Ordering information scheme

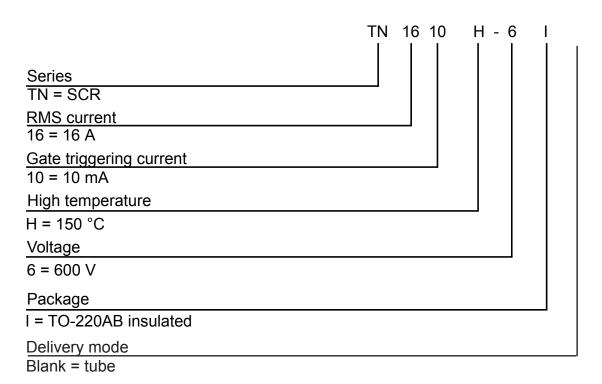


Table 6. Ordering information

Order co	de Mark	ing Package	Weight	Base qty.	Delivery mode
TN1610H	-6I TN161	10H6 TO-220AB I	ns. 2.3 g	50	Tube

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Revision history

Table 7. Document revision history

Date	Revision	Changes
16-Dec-2019	1	Initial release.

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